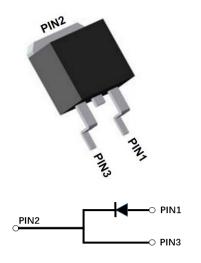






Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F(135°C)}	15A
Q _C	58nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112010BGH
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _c =25°C			31.5
Continuous forward current @ T _C =135°C	I _F	Α	15
Continuous forward current @ T _C =155°C			10
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	90
Power Dissipation@ T _C =25°C	P _{TOT}	W	153
Power Dissipation@ T _C =110°C	ГТОТ	VV	66
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	40.5
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drep	V _F	V	I _F =10A, T _j =25°C	1.38	1.55
Forward voltage drop	VF	V	I _F =10A, T _j =175°C	2	-
Povorce leakage gurrent			V _R =1200V, T _j =25°C	0.5	20
Reverse leakage current	I _R	μA	V _R =1200V, T _j =175°C	8	-
Total capacitive charge	Q _C	nC	$\begin{array}{c} V_R = 800V, \ T_j = 25^{\circ}C \ , \\ Q_C = \int_0^{VR} C(V) dV \end{array}$	58	-
			V _R =0V, f=1MHZ	813	-
Total capacitance	С	pF	V _R =400V, f=1MHZ	54	-
			V _R =800V, f=1MHZ	40	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	15	-

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\scriptscriptstyle{\theta J-C}}$	°C W	0.98

■Typical Characteristics

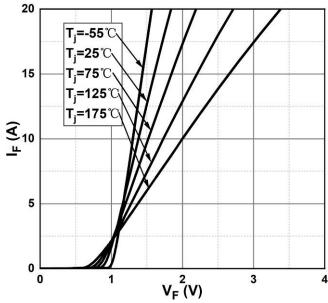


Figure 1. Forward Characteristics

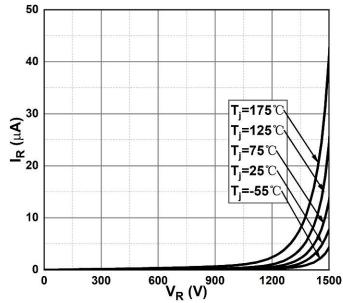
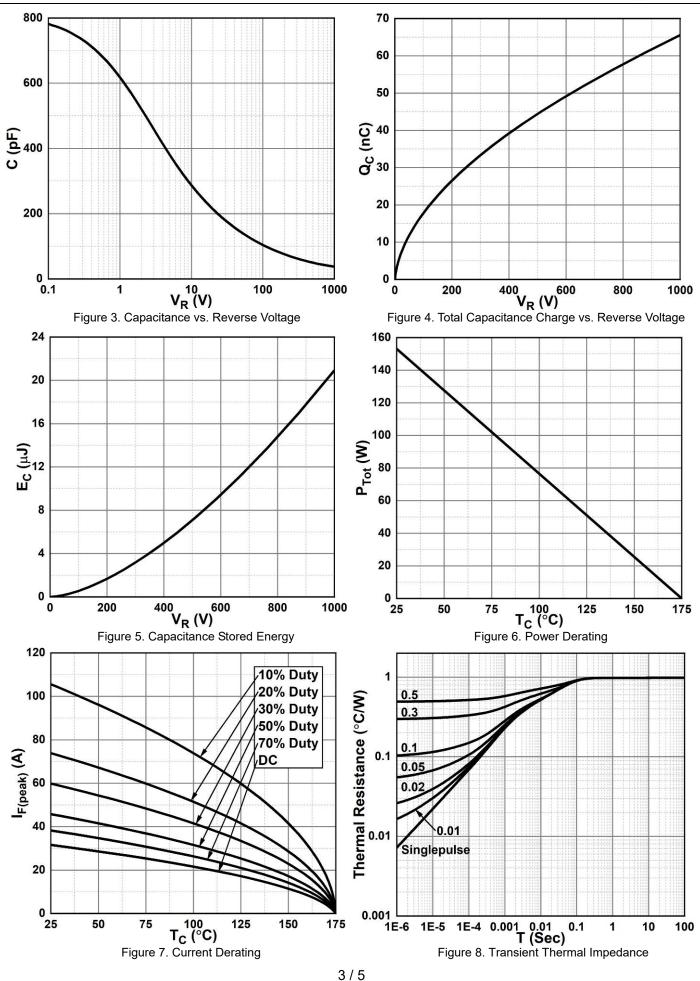


Figure 2. Reverse Characteristics

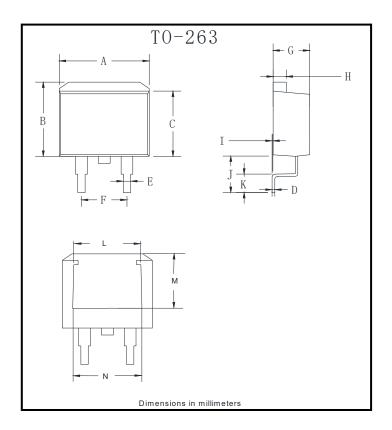








■Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
M	6.2	6.8		
N	7.6	8.2		



YJD112010BGH



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